

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3483	"gate turn off thyristor" "gate turn-off thyristor"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2009/04/24 09:15
L2	663	L1 and "gate electrode"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2009/04/24 09:15
L3	149	2 and "gate electrode" near5 (pad contact)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2009/04/24 09:16
L4	121	2 and "gate electrode" near3 (pad contact)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2009/04/24 09:16
L5	1	3 and (pad contact) near3 (dope doping)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2009/04/24 09:16
L6	100	4 and @ad<"20030409"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2009/04/24 09:18
L7	9	("4086611"   "4171995"   "4198645"   "4231059"   "4581626").PN. OR ("5021855").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/04/24 09:26
L8	40	("4331969"   "4466010"   "4604638"   "4691223"   "4760431"   "4825274"   "4901131"   "4912541"). PN. OR ("4959703"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/04/24 09:33
S1	1	"10552268"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2008/08/07 13:07
S2	3400	"gate turn off thyristor"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2008/08/07 13:16
S3	3409	"gate turn off thyristor" "gate turn-off thyristor"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2008/08/07 13:16
S4	463	S3 and (emitter near3 layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2008/08/07 13:29
S5	204	S4 and (first second) near4 (substrate base)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2008/08/07 13:29

S6	142	S5 and (anode cathode) near4 electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2008/08/07 13:30
S7	126	S6 and @ad<"20030409"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2008/08/07 13:31
S8	3093	(257/E27.052,E27.079, E29.036-E29.038,E29.046- E29.048,E29.115,E29.196, E29.211-E29.225).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2008/08/07 14:22
S9	431	S8 and "gate turn off thyristor"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2008/08/07 14:23
S10	403	S9 and @ad<"20030409"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2008/08/07 14:23
S11	201	S10 and (emitter near3 layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2008/08/07 14:23
S12	143	S11 and (anode cathode) near4 electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2008/08/07 14:24
S13	9	("4086611"   "4171995"   "4198645"   "4231059"   "4581626").PN. OR ("5021855").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/08/07 14:46
S14	2	"20070120145"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2008/08/11 09:09
S15	1	S14 and "low resistance"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2008/08/11 09:10
S16	3400	"gate turn off thyristor"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2008/08/11 10:08
S17	14	S16 and (wide near3 semiconductor) near5 ("silicon carbide" SiC)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2008/08/11 10:08
S18	1	S17 and @ad<"20030409"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2008/08/11 10:08

4/ 24/ 2009 9:43:03 AM

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